

IFU

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE  
(Case No. 213.007-US)

In the Application of: **YE ET AL.**

Serial No: **10/815,573**

Filed: **APRIL 1, 2004**

Title: **SYSTEM AND METHOD OF LITHOGRAPHY  
SIMULATION**

) Group Art Unit: **1756**

) Before Examiner:

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

I hereby certify that this correspondence is  
being deposited with the United States  
Postal Service as first class mail with  
sufficient postage in an envelope  
addressed to the Commissioner for  
Patents, P.O. Box 1450, Alexandria, VA  
22313-1450 on January 5, 2005  
Date

Michiko Sites  
(person signing this certificate)

Michiko Sites  
Signature

**THIRD INFORMATION DISCLOSURE STATEMENT**

Dear Sir:

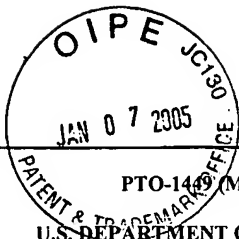
Submitted herewith is one (1) sheet of a modified Form PTO-1449. A copy of each document cited on the attached Form PTO-1449 is also submitted.

It is respectfully requested that the Examiner make his/her consideration of these references formally of record with the initial Office Action.

Respectfully submitted,

Date: January 5, 2005

Neil A. Steinberg, Reg. No. 34,735  
Telephone No. 650-968-8079



PTO-1449 (Modified) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  INFORMATION DISCLOSURE STATEMENT BY APPLICANT	ATTY. DOCKET NO. <b>213.007-US</b>	SERIAL NUMBER <b>10/815,573</b>
	APPLICANT(S) <b>Ye et al.</b>	
	FILING DATE <b>April 1, 2004</b>	GROUP ART UNIT <b>1756</b>

## U.S. PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE

## FOREIGN PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES/NO

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	"Improved Method for Measuring and Assessing Reticle Pinhole Defects for the 100nm Lithography Node", Taylor et al., Photomask Japan 2002, April 2002
	"Mask Defect Disposition: Flux-Area Measurement of Edge, Contact, and OPC Defects Correlates to Wafer and Enables Effective Decisions", Fiekowsky et al., Photomask Japan 2001, Paper 4409-10, April 2001
	"Contact Holes: Optical Area Measurement Predicts Printability and is Highly Repeatable", By Glen Scheid, LSI Logic Corp.; Taylor et al., Photomask Japan 2001, Paper 4409-11, April 2001
	"New Optical Metrology for Masks: Range and Accuracy Rivals SEM", Cottle et al., Photomask Japan 2001, Poster 4409-60, April 2001
	"Soft Defect Printability: Correlation to Optical Flux-Area Measurements", Taylor et al., the SPIE 20 <sup>th</sup> Annual BACUS Symposium on Photomask Technology and Management, Conference 4186, September 2000
	"The End of Thresholds: Subwavelength Optical Linewidth Measurement Using the Flux-Area Technique", Fiekowsky, Photomask Japan 2000, Poster 4066-67, April 2000
	"Defect Printability Measurement in the KLA-351: Correlation to Defect Sizing Using the AVI Metrology System", Fiekowsky et al., the SPIE 19 <sup>th</sup> Annual BACUS Symposium on Photomask Technology and Management, Conference 3873, September 1999
	"Accurate and Repeatable Mask Defect Measurements for Quarter-Micron Technology", Fiekowsky, the SPIE 17 <sup>th</sup> Annual BACUS Symposium on Photomask Technology and Management, September 1997
	"The AVI Photomask Metrology System", Automated Visual Inspection Presentation, February, 2002, 25 pages

EXAMINER	DATE CONSIDERED
EXAMINER: Initial citation if reference was considered. Draw line through citation if not in conformance to MPEP 609 and not considered. Include copy of this form with next communication to applicant.	